

SC Silicon PNP Power Transistor

2SA1011

DESCRIPTION

- · Low Collector Saturation Voltage-
- : $V_{CE(sat)}$ = -0.5V(Typ.)@ I_C = -0.5A
- · Collector-Emitter Breakdown Voltage-
- : V_{(BR)CEO}= -160V(Min.)
- Complement to Type 2SC2344
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

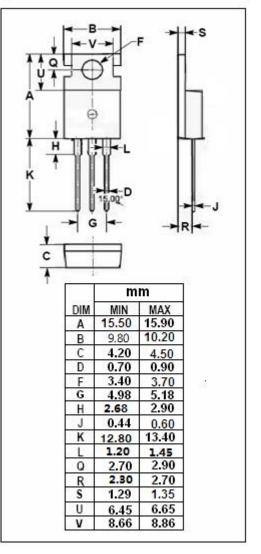
PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-220C package

APPLICATIONS

 Designed for high-voltage switching, audio frequency power amplifiers, 100W output predriver applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|----------------------------------------------|---------|------------------------|
| V _{CBO} | Collector-Base Voltage | -180 | V |
| V _{CEO} | Collector-Emitter Voltage | -160 | V |
| V _{EBO} | Emitter-Base Voltage | -6 | V |
| Ic | Collector Current-Continuous | -1.5 | Α |
| I _{CM} | Collector Current-Peak | -3.0 | Α |
| Pc | Total Power Dissipation@ T _C =25℃ | 25 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}\!\mathbb{C}$ |





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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|------------------------------------------------------------------------|------|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -1mA; R _{BE} = ∞ | -160 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -1mA; I _E = 0 | -180 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = -10mA; I _C = 0 | -6 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -0.5A; I _B = -50mA | | -0.5 | | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = -10mA; V _{CE} = -5V | | -1.5 | | V |
| Ісво | Collector Cutoff Current | V _{CB} = -120V; I _E = 0 | | | -10 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -4V; I _C = 0 | | | -10 | μА |
| h _{FE} | DC Current Gain | I _C = -0.3A; V _{CE} = -5V | 60 | | 200 | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = -50mA ; V _{CE} = -10V | | 100 | | MHz |
| Сов | Output Capacitance | I _E = 0; V _{CB} = -10V; f _{test} = 1.0MHz | | 30 | | pF |

♦ h_{FE} Classifications

| D | E | | |
|--------|---------|--|--|
| 60-120 | 100-200 | | |

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